

Title (en)
METHOD FOR GROWING Si-Ge SEMICONDUCTOR MATERIALS AND DEVICES ON SUBSTRATES

Title (de)
VERFAHREN ZUM ZIEHEN VON SI-GE-HALBLEITERMATERIALIEN UND BAUELEMENTEN AUF SUBSTRATEN

Title (fr)
METHODE DE CROISSANCE PAR EPITAXIE DE MATERIAUX ET DE DISPOSITIFS A SEMI-CONDUCTEURS SI-GE SUR DES SUBSTRATS

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Application
EP 05746524 A 20050408

Priority

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Abstract (en)
[origin: WO2006031257A2] A method is provided for growing Si-Ge materials on Si(100) with Ge-rich contents (Ge>50 at.%) and precise stoichiometries SiGe, SiGe<sub

IPC 8 full level
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Citation (search report)

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